## ADG411/ADG412/ADG413

## FEATURES

44 V supply maximum ratings $\pm 15 \mathrm{~V}$ analog signal range<br>Low on resistance (< $35 \Omega$ )<br>Ultralow power dissipation ( $35 \mu \mathrm{~W}$ )<br>Fast switching times

ton < 175 ns
toff $<\mathbf{1 4 5}$ ns
TTL-/CMOS-compatible
Plug-in replacement for DG411/DG412/DG413

## APPLICATIONS

Audio and video switching
Automatic test equipment
Precision data acquisition
Battery-powered systems
Sample-and-hold systems
Communication systems

## GENERAL DESCRIPTION

The ADG411, ADG412, and ADG413 are monolithic CMOS devices comprising four independently selectable switches. They are designed on an enhanced $\mathrm{LC}^{2}$ MOS process which provides low power dissipation yet gives high switching speed and low on resistance.

The on resistance profile is very flat over the full analog input range ensuring excellent linearity and low distortion when switching audio signals. Fast switching speed coupled with high signal bandwidth also make the parts suitable for video signal switching. CMOS construction ensures ultralow power dissipation, making the parts ideally suited for portable and battery-powered instruments.

The ADG411, ADG412, and ADG413 contain four independent SPST switches. The ADG411 and ADG412 differ only in that the digital control logic is inverted. The ADG411 switches are turned on with a logic low on the appropriate control input, while a logic high is required for the ADG412. The ADG413 has two switches with digital control logic similar to that of the ADG411 while the logic is inverted on the other two switches.

Each switch conducts equally well in both directions when on, and each has an input signal range that extends to the supplies. In the off condition, signal levels up to the supplies are blocked. All switches exhibit break-before-make switching action for use in multiplexer applications. Inherent in the design is low charge injection for minimum transients when switching the digital inputs.

## PRODUCT HIGHLIGHTS

1. Extended signal range

The ADG411, ADG412, and ADG413 are fabricated on an enhanced LC ${ }^{2}$ MOS, giving an increased signal range which extends fully to the supply rails.
2. Ultralow power dissipation
3. Low Ron
4. Break-before-make switching

This prevents channel shorting when the switches are configured as a multiplexer.
5. Single-supply operation

For applications where the analog signal is unipolar, the ADG411, ADG412, and ADG413 can be operated from a single-rail power supply. The parts are fully specified with a single 12 V power supply and remain functional with single supplies as low as 5 V .

## FUNCTIONAL BLOCK DIAGRAMS



SWITCHES SHOWN FOR A LOGIC 1 INPUT
Figure 1. ADG411


SWITCHES SHOWN FOR A LOGIC 1 INPUT
Figure 2. ADG412


SWITCHES SHOWN FOR A LOGIC 1 INPUT
Figure 3. ADG413

Rev. D
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## ADG411/ADG412/ADG413

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## SPECIFICATIONS

## DUAL SUPPLY

$\mathrm{V}_{\mathrm{DD}}=15 \mathrm{~V} \pm 10 \%, \mathrm{~V}_{\mathrm{SS}}=-15 \mathrm{~V} \pm 10 \%, \mathrm{~V}_{\mathrm{L}}=5 \mathrm{~V} \pm 10 \%, \mathrm{GND}=0 \mathrm{~V}$, unless otherwise noted. ${ }^{1}$
Table 1.

| Parameter | $$ |  | $\begin{aligned} & \text { TVersion } \\ & -55^{\circ} \mathrm{C} \text { to } \\ +25^{\circ} \mathrm{C} & +125^{\circ} \mathrm{C} \end{aligned}$ |  | Unit | Test Conditions/Comments |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  |  |  |
| ANALOG SWITCH Analog Signal Range Ron | $\begin{aligned} & 25 \\ & 35 \end{aligned}$ | $V_{D D}$ to $V_{S S}$ <br> 45 | $\begin{aligned} & 25 \\ & 35 \end{aligned}$ | $V_{D D}$ to $V_{S S}$ <br> 45 | V <br> $\Omega$ typ <br> $\Omega$ max | $\begin{aligned} & \mathrm{V}_{\mathrm{D}}= \pm 8.5 \mathrm{~V}, \mathrm{I}_{\mathrm{I}}=-10 \mathrm{~mA} ; \\ & \mathrm{V}_{\mathrm{DD}}=+13.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{SS}}=-13.5 \mathrm{~V} \end{aligned}$ |
| LEAKAGE CURRENTS Source OFF Leakage Is (OFF) <br> Drain OFF Leakage $I_{D}$ (OFF) <br> Channel ON Leakage $\mathrm{I}_{\mathrm{D}}$ Is (ON) | $\begin{aligned} & \pm 0.1 \\ & \pm 0.25 \\ & \pm 0.1 \\ & \pm 0.25 \\ & \pm 0.1 \\ & \pm 0.4 \end{aligned}$ | $\pm 0.25$ <br> $\pm 5$ $\pm 10$ | $\begin{aligned} & \pm 0.1 \\ & \pm 0.25 \\ & \pm 0.1 \\ & \pm 0.25 \\ & \pm 0.1 \\ & \pm 0.4 \end{aligned}$ | $\pm 20$ <br> $\pm 20$ <br> $\pm 40$ | nA typ <br> nA max <br> nA typ <br> nA max <br> nA typ <br> nA max | $\begin{aligned} & \hline \mathrm{V}_{\mathrm{DD}}=+16.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{SS}}=-16.5 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{D}}=+15.5 \mathrm{~V} /-15.5 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{S}}=-15.5 \mathrm{~V} /+15.5 \mathrm{~V} ; \end{aligned}$ <br> Figure 15 $\begin{aligned} & \mathrm{V}_{\mathrm{D}}=+15.5 \mathrm{~V} /-15.5 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{S}}=-15.5 \mathrm{~V} /+15.5 \mathrm{~V} ; \end{aligned}$ <br> Figure 15 $V_{D}=V_{S}=+15.5 \mathrm{~V} /-15.5 \mathrm{~V}$ <br> Figure 16 |
| DIGITAL INPUTS Input High Voltage, $\mathrm{V}_{\mathrm{INH}}$ Input Low Voltage, VINL Input Current linl or linh | $0.005$ | 2.4 <br> 0.8 <br> $\pm 0.5$ | $0.005$ | 2.4 <br> 0.8 <br> $\pm 0.5$ | $V$ min <br> V max <br> $\mu \mathrm{A}$ typ $\mu \mathrm{A}$ max | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {INL }}$ or $\mathrm{V}_{\text {INH }}$ |
| DYNAMIC CHARACTERISTICS ${ }^{2}$ <br> ton <br> toff <br> Break-Before-Make Time Delay, $t_{D}$ (ADG413 Only) <br> Charge Injection <br> OFF Isolation <br> Channel-to-Channel Crosstalk <br> $\mathrm{C}_{\mathrm{s}}$ (OFF) <br> $\mathrm{C}_{\mathrm{D}}$ (OFF) <br> $\mathrm{C}_{\mathrm{D}}, \mathrm{C}_{\mathrm{S}}(\mathrm{ON})$ | $\begin{aligned} & 110 \\ & 100 \\ & 25 \\ & 5 \\ & 68 \\ & 85 \\ & 9 \\ & 9 \\ & 35 \\ & \hline \end{aligned}$ | 175 145 | $\begin{aligned} & 110 \\ & 100 \\ & 25 \\ & 5 \\ & 68 \\ & 85 \\ & 9 \\ & 9 \\ & 35 \\ & \hline \end{aligned}$ | 175 145 | ns typ ns max ns typ ns max ns typ pC typ dB typ dB typ pF typ pF typ pF typ | $\begin{aligned} & \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} ; \\ & \mathrm{V}_{\mathrm{S}}= \pm 10 \mathrm{~V} ; \text { Figure } 17 \\ & \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} ; \\ & \mathrm{V}_{\mathrm{S}}= \pm 10 \mathrm{~V} ; \text { Figure } 17 \\ & \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} ; \\ & \mathrm{V}_{\mathrm{S} 1}=\mathrm{V}_{\mathrm{S} 2}=10 \mathrm{~V} ; \text { Figure } 18 \\ & \mathrm{~V}_{\mathrm{S}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{s}}=0 \Omega, \mathrm{C}_{\mathrm{L}}=10 \mathrm{nF} ; \end{aligned}$ <br> Figure 19 $\mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=1 \mathrm{MHz} ;$ <br> Figure 20 $\mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=1 \mathrm{MHz} ;$ <br> Figure 21 $\mathrm{f}=1 \mathrm{MHz}$ $\mathrm{f}=1 \mathrm{MHz}$ $\mathrm{f}=1 \mathrm{MHz}$ |
| POWER REQUIREMENTS <br> IDD Iss <br> IL | $\begin{aligned} & 0.0001 \\ & 1 \\ & 0.0001 \\ & 1 \\ & 0.0001 \\ & 1 \\ & \hline \end{aligned}$ | 5 5 5 | $\begin{aligned} & 0.0001 \\ & 1 \\ & 0.0001 \\ & 1 \\ & 0.0001 \\ & 1 \\ & \hline \end{aligned}$ | $\begin{gathered} 5 \\ 5 \\ 5 \end{gathered}$ | $\mu \mathrm{A}$ typ $\mu \mathrm{A}$ max $\mu \mathrm{A}$ typ $\mu \mathrm{A}$ max $\mu \mathrm{A}$ typ $\mu \mathrm{A}$ max | $\begin{aligned} & \mathrm{V}_{\mathrm{DD}}=+16.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{SS}}=-16.5 \mathrm{~V} \text {; Digital } \\ & \text { inputs }=0 \mathrm{~V} \text { or } 5 \mathrm{~V} \end{aligned}$ |

[^0]
## ADG411/ADG412/ADG413

## SINGLE SUPPLY

$\mathrm{V}_{\mathrm{DD}}=12 \mathrm{~V} \pm 10 \%, \mathrm{~V}_{\mathrm{SS}}=0 \mathrm{~V}, \mathrm{~V}_{\mathrm{L}}=5 \mathrm{~V} \pm 10 \%, \mathrm{GND}=0 \mathrm{~V}$, unless otherwise noted. ${ }^{1}$
Table 2.

| Parameter | B Version |  | T Version |  | Unit | Test Conditions/Comments |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | $+25^{\circ} \mathrm{C}$ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | $+25^{\circ} \mathrm{C}$ | $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ |  |  |
| ANALOG SIGNAL RANGE Ron |  | 0 V to $\mathrm{V}_{\mathrm{DD}}$ |  | 0 V to $\mathrm{V}_{\mathrm{DD}}$ |  |  |
|  | 40 |  | 40 |  | $\Omega$ typ | $0<\mathrm{V}_{\mathrm{D}}=8.5 \mathrm{~V}, \mathrm{I}_{\mathrm{S}}=-10 \mathrm{~mA}$; |
|  | 80 | 100 | 80 | 100 | $\Omega$ max | $V_{D D}=10.8 \mathrm{~V}$ |
| LEAKAGE CURRENTS Source OFF Leakage IS (OFF) |  |  |  |  |  | $V_{D D}=13.2 \mathrm{~V}$ |
|  | $\pm 0.1$ |  | $\pm 0.1$ |  | nA typ | $\mathrm{V}_{\mathrm{D}}=12.2 \mathrm{~V} / 1 \mathrm{~V}, \mathrm{~V}_{\mathrm{S}}=1 \mathrm{~V} / 12.2 \mathrm{~V}$; |
|  | $\pm 0.25$ | $\pm 5$ | $\pm 0.25$ | $\pm 20$ | nA max | Figure 15 |
| Drain OFF Leakage ID (OFF) | $\pm 0.1$ |  | $\pm 0.1$ |  | nA typ | $\mathrm{V}_{\mathrm{D}}=12.2 \mathrm{~V} / 1 \mathrm{~V}, \mathrm{~V}_{\mathrm{S}}=1 \mathrm{~V} / 12.2 \mathrm{~V}$; |
|  | $\pm 0.25$ | $\pm 5$ | $\pm 0.25$ | $\pm 20$ | $n A$ max | Figure 15 |
| Channel ON Leakage $\mathrm{I}_{\mathrm{D}}, \mathrm{I}_{5}(\mathrm{ON})$ | $\pm 0.1$ |  | $\pm 0.1$ |  | nA typ | $\mathrm{V}_{\mathrm{D}}=\mathrm{V}_{\mathrm{S}}=12.2 \mathrm{~V} / 1 \mathrm{~V}$; |
|  | $\pm 0.4$ | $\pm 10$ | $\pm 0.4$ | $\pm 40$ | nA max | Figure 16 |
| DIGITAL INPUTS |  |  |  |  |  |  |
| Input High Voltage, $\mathrm{V}_{\mathrm{INH}}$ Input Low Voltage, VINL Input Current linL or $l_{\text {INH }}$ |  | 2.4 |  | 2.4 | $V$ min |  |
|  |  | 0.8 |  | 0.8 | $\checkmark$ max |  |
|  |  |  |  |  |  |  |
|  | 0.005 |  | 0.005 |  | $\mu \mathrm{A}$ typ | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {INL }}$ or $\mathrm{V}_{\text {INH }}$ |
|  |  | $\pm 0.5$ |  | $\pm 0.5$ | $\mu \mathrm{A}$ max |  |
| DYNAMIC CHARACTERISTICS² ton |  |  |  |  |  |  |
|  | 175 |  | 175 |  | ns typ | $\mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF}$; |
|  |  | 250 |  | 250 | ns max | $\mathrm{V}_{\mathrm{s}}=8 \mathrm{~V}$; Figure 17 |
| toff | 95 |  | 95 |  | ns typ | $\mathrm{RL}_{\mathrm{L}}=300 \Omega, \mathrm{CL}_{\mathrm{L}}=35 \mathrm{pF}$; |
|  |  | 125 |  | 125 | ns max | $\mathrm{V}_{\mathrm{S}}=8 \mathrm{~V}$; Figure 17 |
| Break-Before-Make Time Delay, to (ADG413 Only) | 25 |  | 25 |  | ns typ | $\mathrm{RL}=300 \Omega, \mathrm{CL}_{\mathrm{L}}=35 \mathrm{pF}$; |
|  |  |  |  |  |  | $\mathrm{V}_{51}=\mathrm{V}_{52}=+10 \mathrm{~V}$; Figure 18 |
| Charge Injection | 25 |  | 25 |  | pC typ | $\mathrm{V}_{\mathrm{S}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{S}}=0 \Omega, \mathrm{C}_{\mathrm{L}}=10 \mathrm{nF} ;$ |
| OFF Isolation |  |  |  |  |  | Reme |
|  | 68 |  | 68 |  | dB typ | $\mathrm{RL}_{\mathrm{L}}=50 \Omega, \mathrm{CL}=5 \mathrm{pF}, \mathrm{f}=1 \mathrm{MHz} ;$ <br> Figure 20 |
| Channel-to-Channel Crosstalk | 85 |  | 85 |  | dB typ | $\mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=1 \mathrm{MHz} ;$ <br> Figure 21 |
| $\mathrm{C}_{s}$ (OFF) | 9 |  | 9 |  | pF typ | $\mathrm{f}=1 \mathrm{MHz}$ |
| $\mathrm{C}_{\mathrm{D}}$ (OFF) | 9 |  | 9 |  | pF typ | $\mathrm{f}=1 \mathrm{MHz}$ |
| $\mathrm{C}_{\mathrm{D}}, \mathrm{C}_{S}(\mathrm{ON})$ | 35 |  | 35 |  | pF typ | $\mathrm{f}=1 \mathrm{MHz}$ |
| POWER REQUIREMENTS |  |  |  |  |  | $\begin{aligned} & \mathrm{V} \mathrm{DD}=13.2 \mathrm{~V} ; \\ & \text { Digital inputs }=0 \mathrm{~V} \text { or } 5 \mathrm{~V} \end{aligned}$ |
| IDD | 0.0001 |  | 0.0001 |  | $\mu \mathrm{A}$ typ |  |
|  |  | 5 |  | 5 | $\mu \mathrm{A}$ max |  |
| IL | 0.0001 |  | 0.0001 |  | $\mu \mathrm{A}$ typ |  |
|  |  | 5 |  | 5 | $\mu \mathrm{A}$ max | $\mathrm{V}_{\mathrm{L}}=5.25 \mathrm{~V}$ |

${ }^{1}$ Temperature ranges are as follows: B versions: $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$; T versions: $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$.
${ }^{2}$ Guaranteed by design; not subject to production test.

Table 3. Truth Table (ADG411/ADG412)

| ADG411 In | ADG412 In | Switch Condition |
| :--- | :--- | :--- |
| 0 | 1 | ON |
| 1 | 0 | OFF |

Table 4. Truth Table (ADG413)

| Logic | Switch 1, 4 | Switch 2, 3 |
| :--- | :--- | :--- |
| 0 | OFF | ON |
| 1 | ON | OFF |

## ADG411/ADG412/ADG413

## ABSOLUTE MAXIMUM RATINGS

$\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$, unless otherwise noted.

Table 5.

| Parameters | Ratings |
| :---: | :---: |
| $V_{\text {DD }}$ to $V_{S S}$ | 44 V |
| VDD to GND | -0.3 V to +25 V |
| Vss to GND | +0.3 V to -25 V |
| VL to GND | -0.3 V to $\mathrm{V}_{\mathrm{DD}}+0.3 \mathrm{~V}$ |
| Analog, Digital Inputs ${ }^{1}$ | $V_{S S}-2 V \text { to } V_{D D}+2 V \text { or }$ 30 mA , whichever occurs first |
| Continuous Current, S or D | 30 mA |
| Peak Current, S or D (Pulsed at 1 ms , 10\% Duty Cycle max) | 100 mA |
| Operating Temperature Range |  |
| Industrial (B Version) | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |
| Extended (TVersion) | $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |
| Junction Temperature | $150^{\circ} \mathrm{C}$ |
| PDIP, Power Dissipation | 470 mW |
| $\theta_{\text {JA }}$ Thermal Impedance | $117^{\circ} \mathrm{C} / \mathrm{W}$ |
| Lead Temperature, Soldering (10 s) | $260^{\circ} \mathrm{C}$ |
| SOIC Package, Power Dissipation | 600 mW |
| $\theta_{\text {JA }}$ Thermal Impedance | $77^{\circ} \mathrm{C} / \mathrm{W}$ |
| TSSOP Package, Power Dissipation | 450 mW |
| $\theta_{\mathrm{JA}}$ Thermal Impedance | $115^{\circ} \mathrm{C} / \mathrm{W}$ |
| Өıc Thermal Impedance | $35^{\circ} \mathrm{C} / \mathrm{W}$ |
| Lead Temperature, Soldering |  |
| Vapor Phase (60 s) | $215^{\circ} \mathrm{C}$ |
| Infrared (15 s) | $220^{\circ} \mathrm{C}$ |

[^1]Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

## ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

## ADG411/ADG412/ADG413

## PIN CONFIGURATION AND FUNCTION DESCRIPTIONS



Table 6. Pin Function Descriptions

| Pin No. | Mnemonic | Description |
| :--- | :--- | :--- |
| $1,8,9,16$ | IN1-IN4 | Logic Control Input. |
| $2,7,10,15$ | D1-D4 | Drain Terminal. Can be an input or output. |
| $3,6,11,14$ | S1-S4 | Source Terminal. Can be an input or output. |
| 4 | VSS $^{2}$ | Most Negative Power Supply Potential in Dual Supplies. In single supply applications, it may be <br> connected to GND. |
| 5 | GND | Ground (0 V) Reference. |
| 12 | VL $^{2}$ | Logic Power Supply (5 V). |
| 13 | Vost Positive Power Supply Potential. |  |

## TYPICAL PERFORMANCE CHARACTERISTICS



Figure 5. On Resistance as a Function of $V_{D}\left(V_{S}\right)$ Dual Supplies


Figure 6. On Resistance as a Function of $V_{D}\left(V_{S}\right)$ for Different Temperatures


Figure 7. Leakage Currents as a Function of Temperature


Figure 8. On Resistance as a Function of $V_{D}\left(V_{S}\right)$ Single Supply


Figure 9. Supply Current vs. Input Switching Frequency


Figure 10. Leakage Currents as a Function of $V_{D}\left(V_{S}\right)$

## ADG411/ADG412/ADG413



Figure 11. Off Isolation vs. Frequency


Figure 12. Crosstalk vs. Frequency

## ADG411/ADG412/ADG413

## TERMINOLOGY

Ron
Ohmic resistance between D and S.

## Is (OFF)

Source leakage current with the switch OFF.

## $\mathrm{I}_{\mathrm{D}}$ (OFF)

Drain leakage current with the switch OFF.

## $\mathrm{I}_{\mathrm{D}}, \mathrm{I}_{\mathrm{s}}(\mathrm{ON})$

Channel leakage current with the switch ON.
$\mathrm{V}_{\mathrm{D}}$ ( V s)
Analog voltage on terminals D, S.
$\mathrm{C}_{s}$ (OFF)
OFF switch source capacitance.

## $\mathrm{C}_{\mathrm{D}}$ (OFF)

OFF switch drain capacitance.
$\mathrm{C}_{\mathrm{b}}, \mathrm{Cs}_{\mathrm{s}}(\mathrm{ON})$
ON switch capacitance.
ton
Delay between applying the digital control input and the output switching on.
toff
Delay between applying the digital control input and the output switching off.
$t_{D}$
OFF time or ON time measured between the $90 \%$ points of both switches, when switching from one address state to another.

## Crosstalk

A measure of unwanted signal which is coupled through from one channel to another as a result of parasitic capacitance.
Off Isolation
A measure of unwanted signal coupling through an OFF switch.

## Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching.

## ADG411/ADG412/ADG413

## APPLICATIONS

Figure 13 illustrates a precise, fast, sample-and-hold circuit. An AD845 is used as the input buffer while the output operational amplifier is an AD711. During the track mode, SW1 is closed and the output Vout follows the input signal $\mathrm{V}_{\text {IN }}$. In the hold mode, SW1 is opened and the signal is held by the hold capacitor $\mathrm{C}_{\mathrm{H}}$.
Due to switch and capacitor leakage, the voltage on the hold capacitor decreases with time. The ADG411/ADG412/ADG413 minimizes this droop due to its low leakage specifications. The droop rate is further minimized by the use of a polystyrene hold capacitor. The droop rate for the circuit shown is typically $30 \mu \mathrm{~V} / \mu \mathrm{s}$.
A second switch, SW2, which operates in parallel with SW1, is included in this circuit to reduce pedestal error. Since both switches are at the same potential, they have a differential effect on the op amp AD711, which minimizes charge injection effects. Pedestal error is also reduced by the compensation network $\mathrm{R}_{\mathrm{C}}$ and $\mathrm{C}_{\mathrm{c}}$. This compensation network also reduces
the hold time glitch while optimizing the acquisition time. Using the illustrated op amps and component values, the pedestal error has a maximum value of 5 mV over the $\pm 10 \mathrm{~V}$ input range. Both the acquisition and settling times are 850 ns .


Figure 13. Fast, Accurate Sample-and-Hold

## TEST CIRCUITS



Figure 17. Switching Times


Figure 18. Break-Before-Make Time Delay


Figure 19. Charge Injection

## ADG411/ADG412/ADG413



Figure 20. Off Isolation


Figure 21. Channel-to-Channel Crosstalk

## OUTLINE DIMENSIONS



Figure 23. 16-Lead Thin Shrink Small Outline Package [TSSOP] (RU-16)
Dimensions shown in millimeters

## ADG411/ADG412/ADG413



ORDERING GUIDE

| Model ${ }^{1}$ | Temperature Range | Package Description | Package Option |
| :---: | :---: | :---: | :---: |
| ADG411BN | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead P-DIP | N-16 |
| ADG411BNZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead P-DIP | N-16 |
| ADG411BR | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG411BR-REEL | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG411BR-REEL7 | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG411BRZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG411BRZ-REEL | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG411BRZ-REEL7 | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG411BRU | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG411BRU-REEL | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG411BRU-REEL7 | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG411BRUZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG411BRUZ-REEL | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG411BRUZ-REEL7 | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG411BCHIPS |  | DIE |  |
| ADG412BN | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead P-DIP | N-16 |
| ADG412BNZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead P-DIP | N-16 |
| ADG412BR | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG412BR-REEL | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG412BR-REEL7 | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG412BRZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG412BRZ-REEL | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG412BRZ-REEL7 | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG412BRU | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG412BRU-REEL | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG412BRU-REEL7 | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG412BRUZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG412BRUZ-REEL | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG412BRUZ-REEL7 | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG413BN | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead P-DIP | N-16 |
| ADG413BNZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead P-DIP | N-16 |
| ADG413BR | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG413BR-REEL | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG413BRZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG413BRZ-REEL | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_N | R-16 |
| ADG413BRUZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG413BRUZ-500RL7 | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG413BRUZ-REEL | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |
| ADG413BRUZ-REEL7 | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead TSSOP | RU-16 |

[^2]
## ADG411/ADG412/ADG413

## NOTES

## Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery \& Lifecycle Information:

Analog Devices Inc.:
ADG411BRZ-REEL ADG412BRUZ-REEL7 ADG413BRZ-REEL ADG413BRUZ ADG412BRZ-REEL7 ADG412BRZ
ADG411BNZ ADG411BRU ADG413BRUZ-REEL ADG413BRUZ-REEL7 ADG411BR-REEL7 ADG413BRZ
ADG411BRUZ ADG412BRZ-REEL ADG412BNZ ADG411BRZ-REEL7 ADG412BR ADG413BNZ ADG411BRUZ-
REEL ADG413BR ADG411BRZ ADG411BRU-REEL7 ADG412BR-REEL ADG411BRUZ-REEL7 ADG412BRUZ
ADG412BRUZ-REEL ADG412BR-REEL7 ADG411BR ADG412BN ADG412BRU-REEL


[^0]:    ${ }^{1}$ Temperature ranges are as follows: B versions: $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$; T versions: $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$.
    ${ }^{2}$ Guaranteed by design; not subject to production test.

[^1]:    ${ }^{1}$ Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

[^2]:    ${ }^{1} Z=$ RoHS Compliant Part.

